

BUK9611-80E

N-channel TrenchMOS logic level FET

5 October 2012

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with Vgst(th) rating of greater than 0.5V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	182	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	8.3	11	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 64 \text{ V};$ Fig. 13; Fig. 14		-	16	-	nC

[1] Continuous current is limited by package.



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	G	gate	mb	D I		
2	D	drain				
3	S	source	1 3	1		G T T
mb	D	mounting base; connected to drain		mbb076 S		
			D2PAK (SOT404)			

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9611-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK9611-80E	BUK9611-80E

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
		T _j ≤ 175 °C; DC		-10	10	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>	[3]	-	75	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	58	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	327	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	182	W
T _{stg}	storage temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drain	diode		'			_
I _S	source current	T _{mb} = 25 °C	[3]	-	75	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	327	Α
Avalanche ru	ggedness		'			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[4][5]	-	145	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Continuous current is limited by package.
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information.

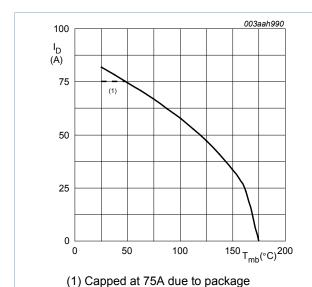
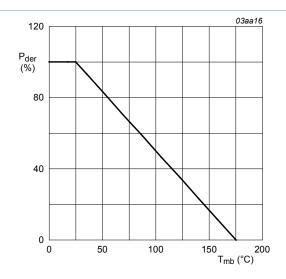


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$



Normalized total power dissipation as a Fig. 2. function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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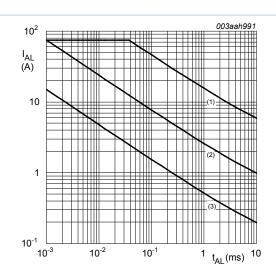
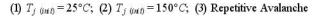


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



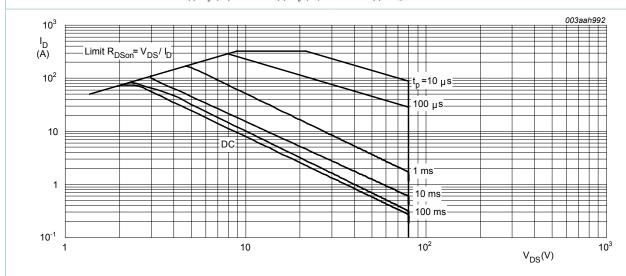


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

6. Thermal characteristics

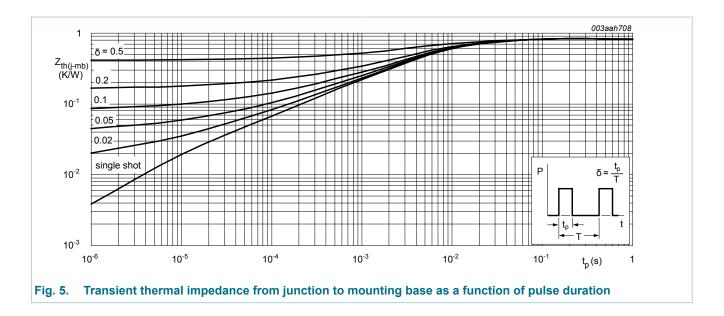
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.82	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		_
V _{(BR)DSS} drain-source breakdown volta		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.03	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 20 A; T _j = 25 °C; <u>Fig. 11</u>	-	8.3	11	mΩ
	resistance	V_{GS} = 10 V; I_D = 20 A; T_j = 25 °C; Fig. 11	-	7.8	10	mΩ
		V _{GS} = 5 V; I _D = 20 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	27.3	mΩ
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 64 V; V _{GS} = 5 V;	-	48.8	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	12.2	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q_{GD}	gate-drain charge			-	16	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	5362	7149	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	350	420	pF
C _{rss}	reverse transfer capacitance			-	185	253	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R_{L} = 3 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω		-	29.6	-	ns
t _r	rise time			-	63.9	-	ns
t _{d(off)}	turn-off delay time			-	58.4	-	ns
t _f	fall time			-	53.2	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die		-	2.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad		-	7.5	-	nΗ
Source-dra	in diode						
V_{SD}	source-drain voltage	$I_S = 20 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; Fig. 16		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	37.7	-	ns
Qr	recovered charge	V _{DS} = 25 V		-	61.5	-	nC

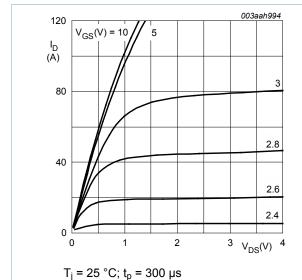


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

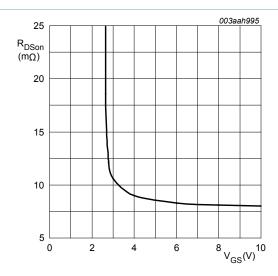


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 20A$$

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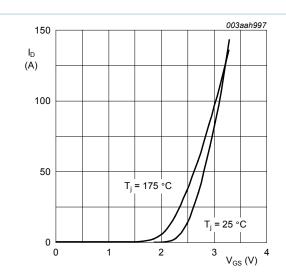


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



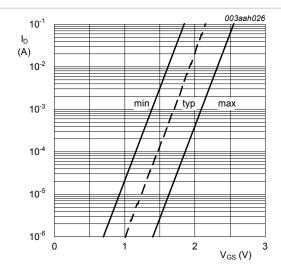


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

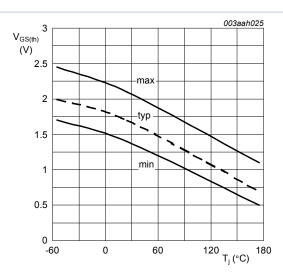
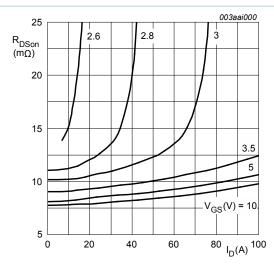


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$



 T_i = 25 °C; t_p = 300 μ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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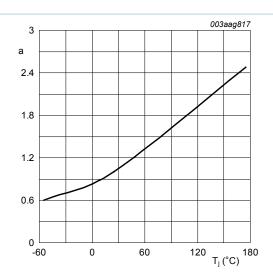


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25~\mathrm{C})}}$$

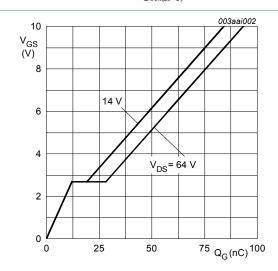


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 20A$$

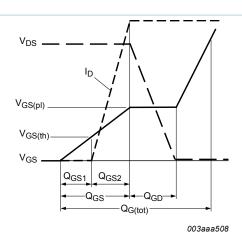


Fig. 13. Gate charge waveform definitions

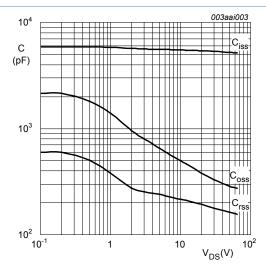


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

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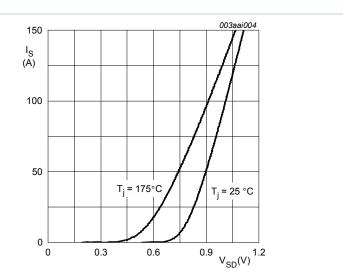


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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8. Package outline

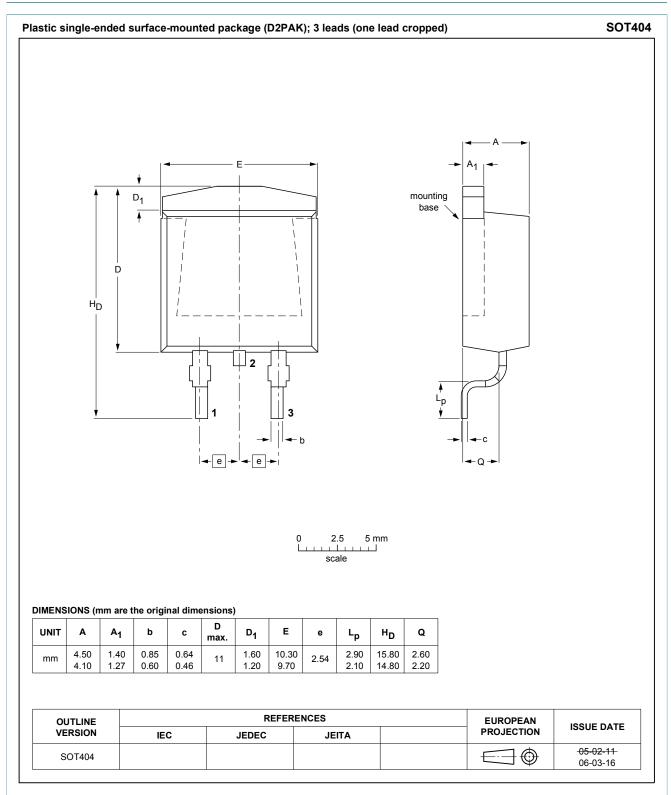


Fig. 17. Package outline D2PAK (SOT404)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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